

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**REVOCATION OF POWER OF ATTORNEY,  
NEW POWER OF ATTORNEY BY ASSIGNEE AND  
CHANGE OF CORRESPONDENCE ADDRESS**

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

**Customer No. 20792**

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

**Customer No. 20792**  
Myers Bigel Sibley & Sajovec, P.A.  
P. O. Box 37428  
Raleigh, North Carolina 27627  
Telephone: (919) 854-1400  
Facsimile: (919) 854-1401

Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patents or patent applications identified to Renesas Technology Corp. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By: Jeong Taek Kong  
Jeong-Taek Kong

Title: Senior Vice President of IP Team

Date: July 7, 2008

# APPENDIX A

Application No.	Patent No.	Filing Date	Assignment Recorded	Reel	Frame	Title of Patent
08/841612	5,870,218	04/30/1997	Hitachi Ltd.	008541	0020	Non-volatile Semiconductor Memory Device Which Stores Multi-Value Information
			Renesas	019287	0688	
			Samsung	021172	0367	
09/096457	5,982,667	06/11/1998	Renesas	019287	0746	Non-volatile Semiconductor Memory Device For Storing Multivalue Information By Controlling Erase And Plural Write States of Each Memory Cell
			Samsung	021172	0367	
09/339960	6,181,603	06/25/1999	Renesas	019287	0750	Non-volatile Semiconductor Memory Device Having Plural Memory Cells Which Store Multi-Value Information
			Samsung	021172	0367	
09/715106	6,396,736	11/20/2000	Renesas	019287	0754	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
			Samsung	021172	0367	
10/154853	6,771,537	05/28/2002	Renesas	014569	0585	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
			Samsung	021172	0367	
10/832311	7,031,187	April 27, 2004	Renesas	021134	0753	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
			Samsung	021172	0367	
11/332206	7,245,532	January 17, 2006	Samsung	021172	0367	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
11/595880	7,394,697	November 13, 2006	Samsung	021172	0367	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value

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12/117918		May 9, 2008	Renesas	021134	0584	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
			Samsung	021172	0367	
07/704739	5,300,802	May 20, 1991	Renesas	021076	0845	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
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08/422940	5,629,541	April 17, 1995	Renesas	021076	0845	Semiconductor Memory Device Constituted by Single Transistor Type Non-volatile Cells and Facilitated for Both Electrical Erasing and Writing of Data
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			Samsung	021172	0367	
09/282204	6,255,690	March 31, 1999	Renesas	021076	0845	Non-volatile Semiconductor Memory Device
			Samsung	021172	0367	

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09/873451	6,451,643	June 5, 2001	Renesas	021076	0845	Method of Manufacturing a Semiconductor Device Having Non-volatile Memory Cell Portion with Single Transistor Type Memory Cells and Peripheral Portion with MISFETs
10/164626	6,777,282	June 10, 2002	Renesas	014569	0585	Method of Manufacturing a Semiconductor Memory Device Having a Memory Cell Portion Including MISFETs With a Floating Gate and a Peripheral Circuit Portion With MISFETs
10/819205	6,960501	April 7, 2004	Renesas	021076	0845	Method of Manufacturing a Semiconductor Memory Device Having a Non-volatile Memory Cell Portion with Single MISFET Transistor Type Memory Cells and a Peripheral Circuit Portion with MISFETs
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11/393774	7,399,667	March 31, 2006	Renesas	021076	0845	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
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07/765065	5,189,497	September 24, 1991	Renesas	021076	0845	Semiconductor Memory Device
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07/992473	5,340,760	December 15, 1992	Renesas	021076	0845	Method of Manufacturing EEPROM Memory Device
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08/419232	5,604,142	April 10, 1995	Renesas	021076	0845	Method of Making an EEPROM With Peripheral Transistor
			Samsung	021172	0367	
11/082992	7,242,611	March 18, 2005	Renesas	016400	0869	Nonvolatile Semiconductor Memory Device for Writing Multivalued Data
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11/819015		June 25, 2007	Renesas	016400	0869	Nonvolatile Semiconductor Memory Device for Writing Multivalued Data
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11/819016		June 25, 2007	Renesas	016400	0869	Non-volatile Semiconductor Memory Device for Writing Multivalued Data
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09/620719	6,496,409	July 20, 2000	Mitsubishi	010954	0262	Variable Capacity Semiconductor Memory

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			Renesas	021118	0337	Device
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			Renesas	021029	0409	
			Samsung	021172	0367	
10/700592	7,068,541	November 5, 2003	Renesas	014682	0411	Nonvolatile Memory and Method of Erasing for Nonvolatile Memory
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